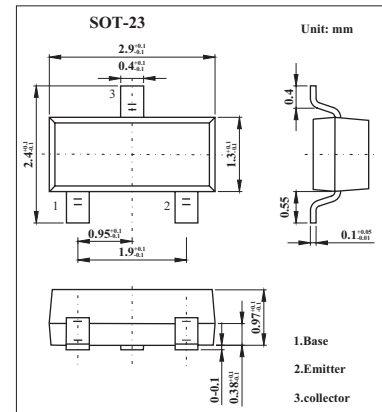


Medium Power Transistor

2SA1036K

■ Features

- Large I_c . $I_{cMax.} = -500mA$
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-40	V
Collector-emitter voltage	V_{CEO}	-32	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current *	I_c	-0.5	A
Collector power dissipation	P_c	0.2	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* P_c max. must not be exceeded.

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_c = -100 \mu A$	-40			V
Collector-emitter breakdown voltage	V_{CEO}	$I_c = -1 mA$	-32			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -20 V$			-1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4 V$			-1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -100 mA, I_B = -10 mA$			-0.4	V
DC current gain	h_{FE}	$V_{CE} = -3 V, I_c = -10 mA$	82		390	
Output capacitance	C_{ob}	$V_{CB} = -10 V, I_E = 0A, f = 1 MHz$		7		pF
Transition frequency	f_T	$V_{CE} = -5 V, I_E = 20 mA, f = 100 MHz$		200		MHz

■ h_{FE} Classification

Marking	HP	HQ	HR
Rank	P	Q	R
h_{FE}	82~180	120~270	180~390